BLF7G27L-150P; BLF7G27LS-150P

Power LDMOS transistor

Rev. 2 — 12 July 2013

Product data sheet

1. Product profile

1.1 General description

150 W LDMOS power transistor for base station applications at frequencies from 2500 MHz to 2700 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Mode of operation	f (MHz)	I _{Dq} (mA)		` '	•	-	ACPR _{885k} (dBc)	ACPR _{5M} (dBc)
IS-95	2500 to 2700	1200	28	30	16.5	26	-47 <u>[1]</u>	-
Single carrier W-CDMA	2500 to 2700	1200	28	45	16.5	31	-	-38 ^[2]

^[1] Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R_{th} providing excellent thermal stability
- Designed for broadband operation (2500 MHz to 2700 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 2500 MHz to 2700 MHz frequency range



^{[2] 3}GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF. Channel bandwidth is 3.84 MHz.

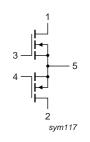
2. Pinning information

Table 2. Pinning

	3			
Pin	Description		Simplified outline	Graphic symbol
BLF7G27	L-150P (SOT539A)			
1	drain1			
2	drain2		1 2	1
3	gate1		5	3
4	gate2		3 4	5
5	source	<u>[1]</u>		4 7
				'
				2 sym117
				sym11.

BLF7G27	'LS-150P (SOT539B)	
1	drain1	
2	drain2	
3	gate1	
4	gate2	
5	source	<u>[1]</u>





[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package						
Type Humber	Γαυκαί	,c	_				
	Name	Description	Version				
BLF7G27L-150P	-	flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads	SOT539A				
BLF7G27LS-150P	-	earless flanged balanced LDMOST ceramic package; 4 leads	SOT539B				

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
I _D	drain current		-	37	Α
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	225	°C

BLF7G27L-150P_7G27LS-150P

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 30 W	0.25	K/W

6. Characteristics

Table 6. Characteristics

 $T_i = 25$ °C unless otherwise specified.

,						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS} \\$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 100 \text{ mA}$	1.3	1.9	2.3	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	5	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	16.75	19	-	Α
I _{GSS}	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	500	nΑ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 3.57 \text{ A}$	-	0.86	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 3.5 \text{ A}$	-	0.14	-	Ω

7. Test information

Remark: All testing performed in a class-AB production test circuit.

Table 7. Functional test information

Mode of operation: 1-carrier N-CDMA, single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF, channel bandwidth is 1.2288 MHz; f_1 = 2500 MHz; f_2 = 2700 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 1200 mA; T_{case} = 25 °C; unless otherwise specified.

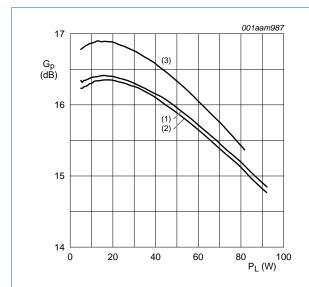
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$P_{L(AV)}$	average output power		-	30	-	W
Gp	power gain		14.8	16.5	-	dB
RL _{in}	input return loss		-	-10	-	dB
η_{D}	drain efficiency		22	26	-	%
ACPR _{885k}	adjacent channel power ratio (885 kHz)		-43	-47	-	dBc

7.1 Ruggedness in class-AB operation

The BLF7G27L-150P and BLF7G27LS-150P are capable of withstanding a load mismatch corresponding to VSWR = 20: 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 1200 \text{ mA}$; $P_L = 35 \text{ W}$ (IS-95); f = 2500 MHz.

7.2 Single carrier IS-95

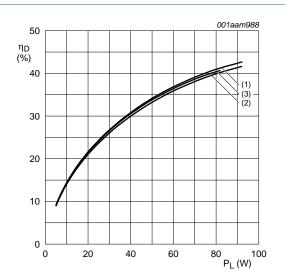
Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1200 \text{ mA}.$

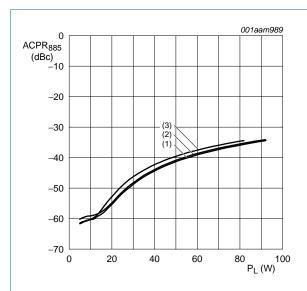
- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Single carrier IS-95 power gain as a function of load power; typical values



- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

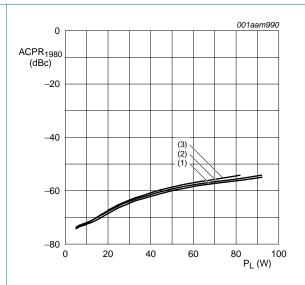
Fig 2. Single carrier IS-95 drain efficiency as a function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1200 \text{ mA}.$

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

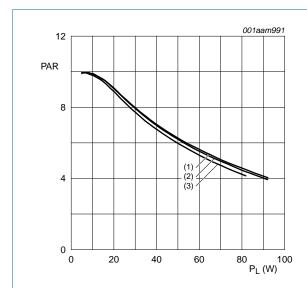
Fig 3. Single carrier IS-95 ACPR at 885 kHz as a function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1200 \text{ mA}.$

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

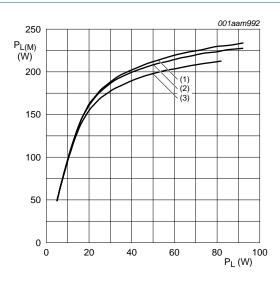
Fig 4. Single carrier IS-95 ACPR at 1980 kHz as a function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1200 \text{ mA}.$

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

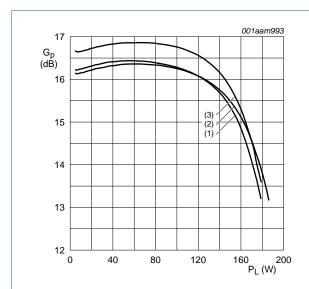
Fig 5. Single carrier IS-95 peak-to-average power ratio as a function of load power; typical values



- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Fig 6. Single carrier IS-95 peak power as a function of load power; typical values

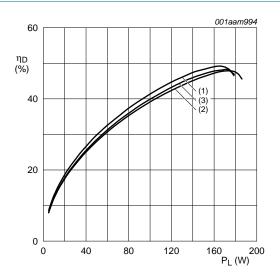
7.3 Pulsed CW



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1200 \text{ mA}.$

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Fig 7. Pulsed CW power gain as a function of load power; typical values

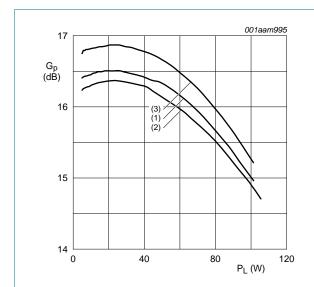


- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Fig 8. Pulsed CW drain efficiency as a function of load power; typical values

7.4 Single carrier W-CDMA

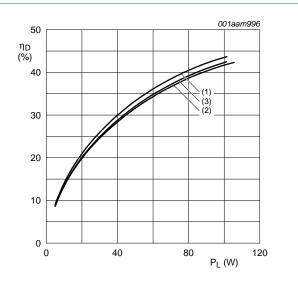
3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF. Channel bandwidth is 3.84 MHz.



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1200 \text{ mA}.$

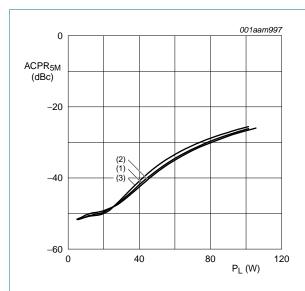
- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Fig 9. Single carrier W-CDMA power gain as a function of load power; typical values



- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

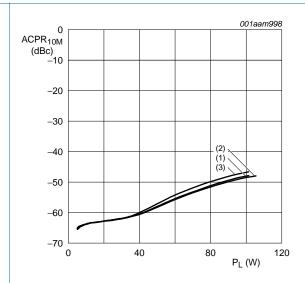
Fig 10. Single carrier W-CDMA drain efficiency as a function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1200 \text{ mA}.$

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

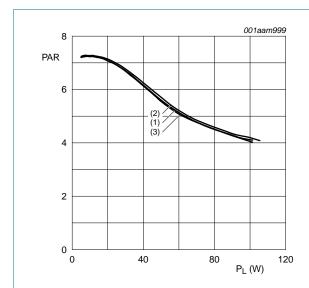
Fig 11. Single carrier W-CDMA ACPR at 5 MHz as a function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1200 \text{ mA}.$

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

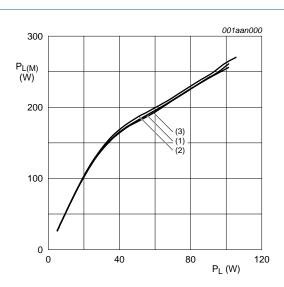
Fig 12. Single carrier W-CDMA ACPR at 10 MHz as a function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1200 \text{ mA}.$

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Fig 13. Single carrier W-CDMA peak-to-average power ratio as a function of load power; typical values



- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Fig 14. Single carrier W-CDMA peak output power as a function of load power; typical values

8. Package outline

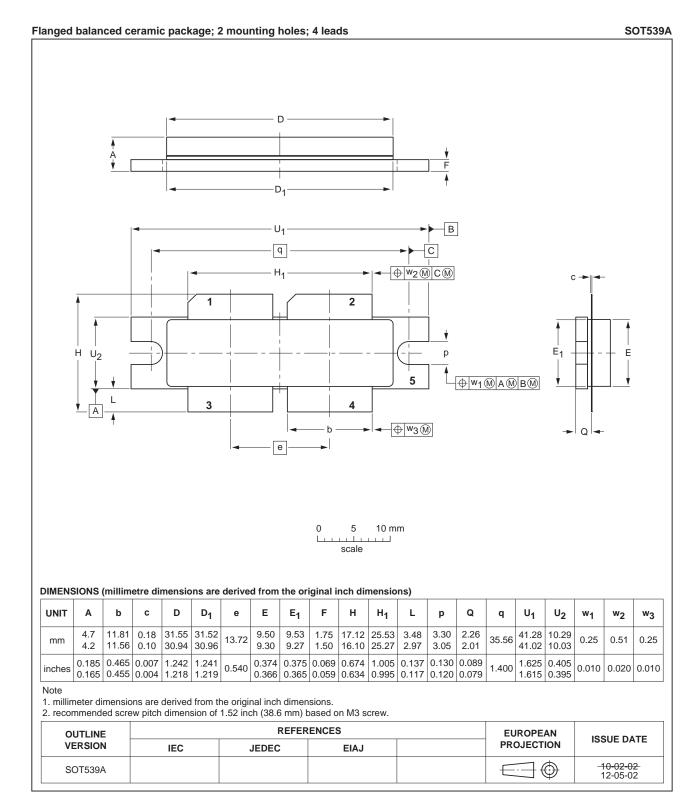


Fig 15. Package outline SOT539A

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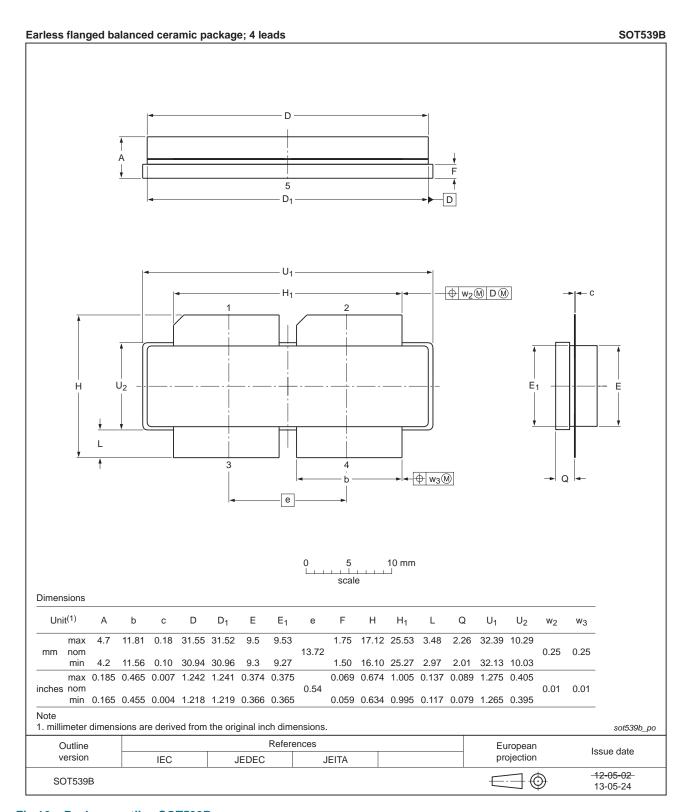


Fig 16. Package outline SOT539B

BLF7G27L-150P_7G27LS-150P

9. Abbreviations

Table 8. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
IS-95	Interim Standard 95
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
N-CDMA	Narrowband Code Division Multiple Access
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF7G27L-150P_7G27LS-150P v.2	20130712	Product data sheet	-	BLF7G27L-150P_7G27LS-150P v.1
Modifications:	The pa	ackage outline Figure	16 is updated.	
	Transl	ation disclaimer adde	ed to the legal tex	t.
BLF7G27L-150P_7G27LS-150P v.1	20101112	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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Power LDMOS transistor

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Power LDMOS transistor

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